



For immediate release

Diodes Incorporated Announces Tiny Transistors that Aid Product Miniaturization

Dallas, Texas –June 17, 2010 --- Diodes Incorporated (Nasdaq: DIOD), a leading global manufacturer and supplier of high-quality application specific standard products within the broad discrete, logic and analog semiconductor markets, today has introduced 20V NPN and PNP bipolar transistors in the ultra-small DFN1411-3 surface mount package that deliver a dramatic increase in the power density and efficiency of power management circuits. These transistors have been designed on Diodes' Generation 5 matrix emitter Bipolar process.

With a footprint measuring just 1.1mm x 1.4mm and an off-board height of 0.5mm, the complementary ZXTN26020DMF and ZXTP26020DMF devices enable portable product miniaturization while offering improvements in both electrical and thermal performance.

Suiting MOSFET and IGBT gate driving, DC-DC conversion and general switching duties, the miniature transistors are a space-saving alternative to much larger SOT23 packaged parts and provide excellent thermal performance, having a minimum FR-4 PCB power dissipation rating of 0.38W for its footprint.

High gain, low saturation and fast switching devices, the bipolars are also characterized by a very high continuous current handling capability. The maximum collector current ratings of 1.5A for the NPN and –1.25A for the PNP are not available from any smaller package device. Further information can be found at the Company's website at <http://www.diodes.com>.

About Diodes Incorporated

Diodes Incorporated (Nasdaq: DIOD), a Standard and Poor's SmallCap 600 and Russell 3000 Index company, is a leading global manufacturer and supplier of high-quality application specific standard products within the broad discrete, logic, and analog semiconductor markets. Diodes serves the consumer electronics, computing, communications, industrial, and automotive markets. Diodes' products include diodes, rectifiers, transistors, MOSFETs, protection devices, functional specific arrays, single gate logic, amplifiers and comparators, Hall-effect and temperature sensors; power management devices, including LED drivers, DC-DC switching and linear voltage regulators, and voltage references along with special function devices, such as USB power switches, load switches, voltage supervisors, and motor controllers. The Company's corporate headquarters, logistics center, and Americas' sales office are located in Dallas, Texas. Design, marketing, and engineering centers are located in Dallas; San Jose, California; Taipei, Taiwan; Manchester, England; and Neuhaus, Germany. The Company's wafer fabrication facilities are located in Kansas City, Missouri and Manchester, with two manufacturing facilities located in Shanghai, China, another in Neuhaus, and a joint venture facility located in Chengdu, China. Additional engineering, sales, warehouse, and logistics offices are located in Taipei; Hong Kong; Manchester; and Munich, Germany; with support offices located throughout the world. For further information, including SEC filings, visit the Company's website at <http://www.diodes.com>.

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